

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[IXYS Corporation](#)

[MCC21-12IO8B](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

Thyristor Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

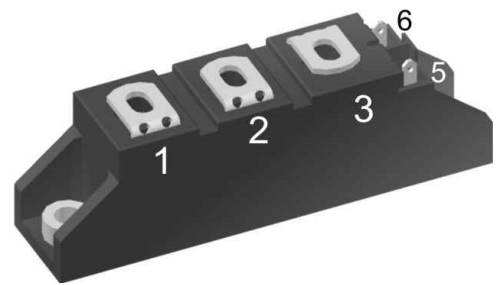
$$I_{TAV} = 21 \text{ A}$$

$$V_T = 1,52 \text{ V}$$


Phase leg

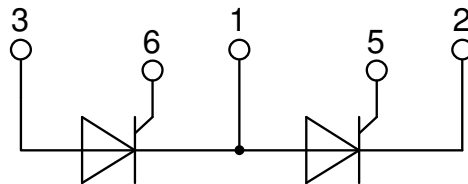
Part number

MCC21-12io8B



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

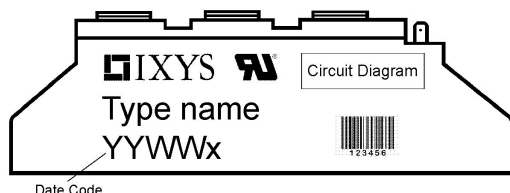
- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Thyristor				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		100	μA	
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		5	mA	
V_T	forward voltage drop	$I_T = 45 A$	$T_{VJ} = 25^{\circ}C$		1,45	V	
		$I_T = 90 A$			1,89	V	
		$I_T = 45 A$	$T_{VJ} = 125^{\circ}C$		1,52	V	
		$I_T = 90 A$			2,20	V	
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$		21	A	
$I_{T(RMS)}$	RMS forward current	180° sine			33	A	
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$		0,85	V	
r_T	slope resistance				15	m Ω	
R_{thJC}	thermal resistance junction to case				1,1	K/W	
R_{thCH}	thermal resistance case to heatsink			0,20		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		90	W	
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		320	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		345	A	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		270	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		295	A	
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		510	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		495	A ² s	
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$		365	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		360	A ² s	
C_J	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		22	pF	
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 125^{\circ}C$		10	W	
		$t_p = 300 \mu s$			5	W	
P_{GAV}	average gate power dissipation				0,5	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 45 A$		150	A/ μs	
		$t_p = 200 \mu s; di_G/dt = 0,45 A/\mu s;$	non-repet., $I_T = 21 A$		500	A/ μs	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		1000	V/ μs	
		$R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$					
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1	V	
			$T_{VJ} = -40^{\circ}C$		1,2	V	
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		65	mA	
			$T_{VJ} = -40^{\circ}C$		80	mA	
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0,2	V	
I_{GD}	gate non-trigger current				5	mA	
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		150	mA	
		$I_G = 0,3 A; di_G/dt = 0,3 A/\mu s$					
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA	
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs	
		$I_G = 0,3 A; di_G/dt = 0,3 A/\mu s$					
t_q	turn-off time	$V_R = 100 V; I_T = 15 A; V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 100^{\circ}C$		150	μs	
		$di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 300 \mu s$					



MCC21-12io8B

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				200	A
T_{VJ}	virtual junction temperature			-40		125	°C
T_{op}	operation temperature			-40		100	°C
T_{stg}	storage temperature			-40		125	°C
Weight					81		g
M_D	mounting torque			2,5		4	Nm
M_T	terminal torque			2,5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13,0	9,7			mm
$d_{Spb/Apb}$		terminal to backside	16,0	16,0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600			V
		t = 1 minute		3000			V



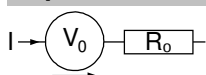
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC21-12io8B	MCC21-12io8B	Box	6	

Similar Part	Package	Voltage class
MCMA25P1200TA	TO-240AA-1B	1200
MCMA35P1200TA	TO-240AA-1B	1200

Equivalent Circuits for Simulation

* on die level

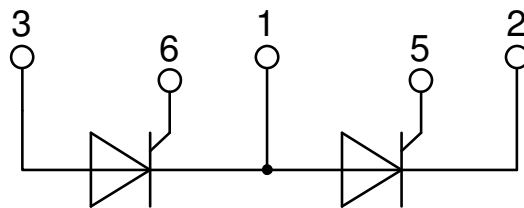
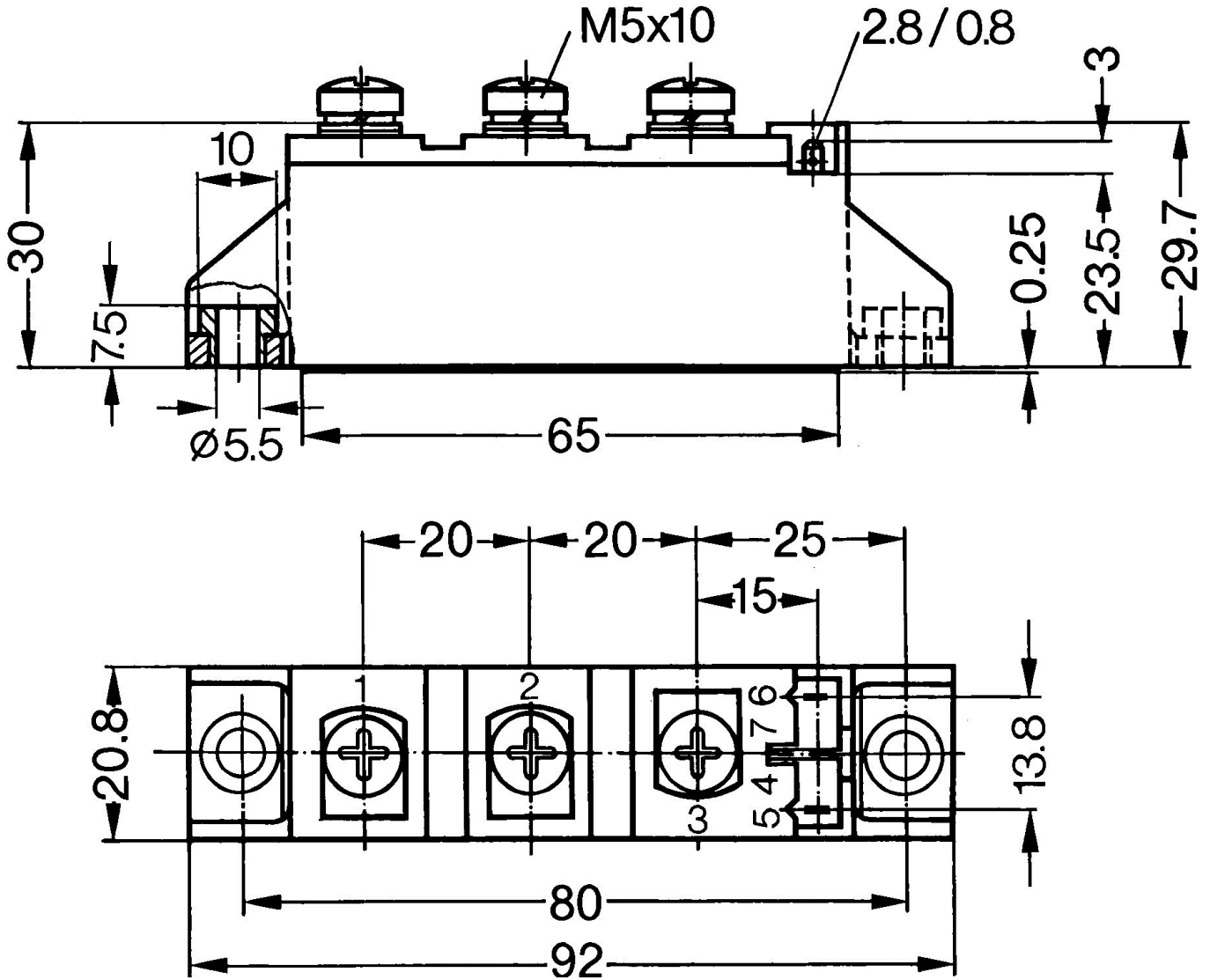
$T_{VJ} = 125^\circ\text{C}$



Thyristor

$V_{0\ max}$	threshold voltage	0,85	V
$R_{0\ max}$	slope resistance *	13,8	mΩ

Outlines TO-240AA



Thyristor

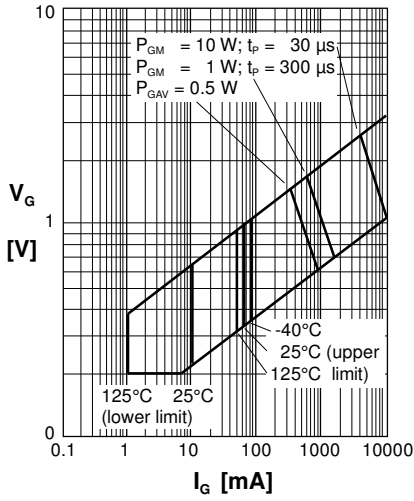


Fig. 1 Gate trigger characteristics

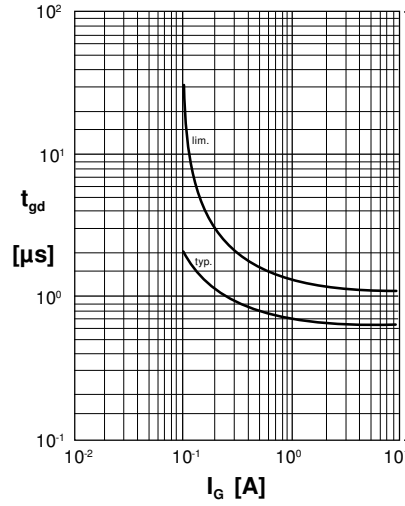


Fig. 2 Gate trigger delay time